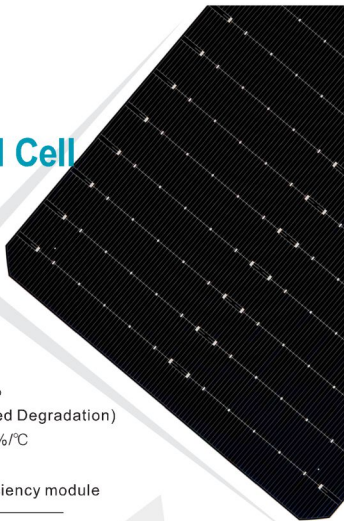




P-Type Mono Bifacial Cell

DAS-PM6D9B



Product Feature

- High conversion efficiency, Up to 23.0%
- Bifaciality $\geq 70\%$
- LID (Light Induced Degradation) $\leq 2.5\%$
- High resistance of PID (Potential Induced Degradation)
- Power temperature coefficient $\leq -0.38\%/^{\circ}\text{C}$
- Weak light response ($200\text{W}/\text{m}^2$) $\geq 95\%$
- Lower CTM loss, better for the high efficiency module



Quality Control

- Efficiency test accuracy is $\pm 0.1\%$
- 100% automatic inspection of IV/EL/Appearance
- Calibration Cell source to Fraunhofer ISE



Management System Certification

- ISO 9001:2015 Quality Management System
- ISO 14001:2015 Environmental Management System
- ISO 45001:2018 Occupational Health and Safety Management System



Product Features

Dimension	166mmx166mm±0.25mm, Φ223mm±0.25mm
Cell Thickness	180μm±20μm
Front side	0.1±0.05mm wide bus bars, 116 finger grids, SiN
Back side	1.8±0.3mm wide discontinuous soldering pads, 156 Aluminum fingers, SiN

Temperature Coefficients

Current Temperature Coefficient	Tkcurrent: +0.048 %/K
Voltage Temperature Coefficient	Tkvoltage: -0.31 %/K
Power Temperature Coefficient	Tkpower: -0.38 %/K

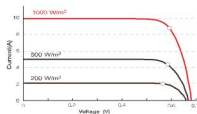
Electrical Data

Eff(%)	Pmpp(W)	Umpp(V)	Impp(A)	Uoc(V)	Isc(A)	FF(%)
23.0	6.31	0.595	10.597	0.686	11.317	81.22
22.9	6.28	0.593	10.587	0.685	11.295	81.14
22.8	6.25	0.591	10.576	0.684	11.273	81.06
22.7	6.22	0.589	10.566	0.683	11.251	80.98
22.6	6.20	0.587	10.555	0.682	11.230	80.90
22.5	6.17	0.585	10.544	0.681	11.208	80.82
22.4	6.14	0.583	10.533	0.680	11.186	80.73
22.3	6.11	0.581	10.522	0.679	11.164	80.65
22.2	6.09	0.579	10.511	0.678	11.143	80.56
22.1	6.06	0.577	10.500	0.677	11.121	80.47
22.0	6.03	0.575	10.489	0.676	11.099	80.39

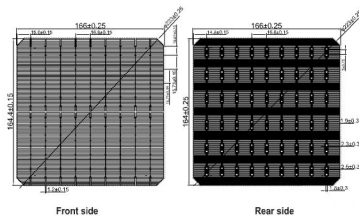
• Standard Test Conditions: 1000W/m², AM 1.5, 25°C

Specifications and data are only for reference.

IV Curve



Dimension



Spectral Response (SR)

